

BZB84 series

Dual Zener diodes

Rev. 03 — 9 June 2009

Product data sheet

1. Product profile

1.1 General description

General-purpose Zener diodes in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Non-repetitive peak reverse power dissipation: ≤ 40 W
- Total power dissipation: ≤ 300 mW
- Two tolerance series:
B = ± 2 % and C = ± 5 %
- Wide working voltage range:
nominal 2.4 V to 75 V (E24 range)
- Small plastic package suitable for surface-mounted design
- Dual common anode configuration
- AEC-Q101 qualified

1.3 Applications

- General regulation functions

1.4 Quick reference data

Table 1. Quick reference data

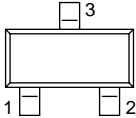
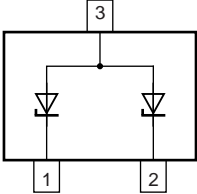
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---|---------------|-------|-----|-----|------|
| Per diode | | | | | | |
| V_F | forward voltage | $I_F = 10$ mA | [1] - | - | 0.9 | V |
| P_{ZSM} | non-repetitive peak reverse power dissipation | | [2] - | - | 40 | W |

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

[2] $t_p = 100$ μ s; square wave; $T_j = 25$ °C prior to surge

2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------------|---|---|
| 1 | cathode (diode 1) |  |  |
| 2 | cathode (diode 2) | | |
| 3 | common anode | | |

006aaa154

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--|---------|--|---------|
| | Name | Description | Version |
| BZB84-B2V4 to BZB84-C75 ^[1] | - | plastic surface-mounted package; 3 leads | SOT23 |

[1] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] | Type number | Marking code ^[1] |
|-------------|-----------------------------|-------------|-----------------------------|
| BZB84-B2V4 | V9* | BZB84-C2V4 | U9* |
| BZB84-B2V7 | VA* | BZB84-C2V7 | UA* |
| BZB84-B3V0 | VB* | BZB84-C3V0 | UB* |
| BZB84-B3V3 | VC* | BZB84-C3V3 | UC* |
| BZB84-B3V6 | VD* | BZB84-C3V6 | UD* |
| BZB84-B3V9 | VE* | BZB84-C3V9 | UE* |
| BZB84-B4V3 | VF* | BZB84-C4V3 | UF* |
| BZB84-B4V7 | VG* | BZB84-C4V7 | UG* |
| BZB84-B5V1 | VH* | BZB84-C5V1 | UH* |
| BZB84-B5V6 | VK* | BZB84-C5V6 | UK* |
| BZB84-B6V2 | VL* | BZB84-C6V2 | UL* |
| BZB84-B6V8 | VM* | BZB84-C6V8 | UM* |
| BZB84-B7V5 | VN* | BZB84-C7V5 | UN* |
| BZB84-B8V2 | VP* | BZB84-C8V2 | UP* |
| BZB84-B9V1 | VR* | BZB84-C9V1 | UR* |

Table 4. Marking codes ...continued

| Type number | Marking code ^[1] | Type number | Marking code ^[1] |
|-------------|-----------------------------|-------------|-----------------------------|
| BZB84-B10 | VS* | BZB84-C10 | US* |
| BZB84-B11 | VT* | BZB84-C11 | UT* |
| BZB84-B12 | VU* | BZB84-C12 | UU* |
| BZB84-B13 | VV* | BZB84-C13 | UV* |
| BZB84-B15 | VW* | BZB84-C15 | UW* |
| BZB84-B16 | PT* | BZB84-C16 | PB* |
| BZB84-B18 | PU* | BZB84-C18 | PC* |
| BZB84-B20 | RP* | BZB84-C20 | RQ* |
| BZB84-B22 | PV* | BZB84-C22 | PD* |
| BZB84-B24 | PW* | BZB84-C24 | PE* |
| BZB84-B27 | PX* | BZB84-C27 | PF* |
| BZB84-B30 | PY* | BZB84-C30 | PG* |
| BZB84-B33 | PZ* | BZB84-C33 | PH* |
| BZB84-B36 | RA* | BZB84-C36 | PJ* |
| BZB84-B39 | RB* | BZB84-C39 | PK* |
| BZB84-B43 | RC* | BZB84-C43 | PL* |
| BZB84-B47 | RD* | BZB84-C47 | PM* |
| BZB84-B51 | RE* | BZB84-C51 | PN* |
| BZB84-B56 | RF* | BZB84-C56 | PP* |
| BZB84-B62 | RG* | BZB84-C62 | PQ* |
| BZB84-B68 | RH* | BZB84-C68 | PR* |
| BZB84-B75 | RJ* | BZB84-C75 | PS* |

[1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---|------------|-------|---|------|
| Per diode | | | | | |
| I_F | forward current | | - | 200 | mA |
| I_{ZSM} | non-repetitive peak reverse current | | [1] - | see Table 8 , 9 , 10 and 11 | |
| P_{ZSM} | non-repetitive peak reverse power dissipation | | [1] - | 40 | W |

Table 5. Limiting values ...continued*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|-------------------------|-----------------------------|-------|------|------|
| Per device | | | | | |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ °C}$ | [2] - | 300 | mW |
| T_j | junction temperature | | - | 150 | °C |
| T_{amb} | ambient temperature | | -55 | +150 | °C |
| T_{stg} | storage temperature | | -65 | +150 | °C |

[1] $t_p = 100\ \mu\text{s}$; square wave; $T_j = 25\text{ °C}$ prior to surge

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--|--|-------------|-------|-----|-----|------|
| Per device; single diode loaded | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] - | - | 417 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | [2] - | - | 100 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Soldering points at pins 1 and 2.

7. Characteristics

Table 7. Characteristics *$T_j = 25\text{ °C}$ unless otherwise specified.*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|-----------------|----------------------|-------|-----|-----|------|
| Per diode | | | | | | |
| V_F | forward voltage | $I_F = 10\text{ mA}$ | [1] - | - | 0.9 | V |

[1] Pulse test: $t_p \leq 300\ \mu\text{s}$; $\delta \leq 0.02$.

Table 8. Characteristics per type; BZB84-B2V4 to BZB84-B24 $T_j = 25\text{ °C}$ unless otherwise specified.

| BZB84-Bxxx | Working voltage V_Z (V) | | Differential resistance r_{dif} (Ω) | | Reverse current I_R (μA) | | Temperature coefficient S_Z (mV/K) | | Diode capacitance C_d (pF) ^[1] | Non-repetitive peak reverse current I_{ZSM} (A) ^[2] |
|------------|------------------------------|-------|--|---------------------|--|-----------|---|------|--|---|
| | $I_Z = 5\text{ mA}$ | | $I_Z = 1\text{ mA}$ | $I_Z = 5\text{ mA}$ | Max | V_R (V) | $I_Z = 5\text{ mA}$ | | | |
| | Min | Max | Max | Max | | | Min | Max | Max | Max |
| 2V4 | 2.35 | 2.45 | 600 | 100 | 50 | 1 | -3.5 | 0 | 450 | 6.0 |
| 2V7 | 2.65 | 2.75 | 600 | 100 | 20 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V0 | 2.94 | 3.06 | 600 | 95 | 10 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V3 | 3.23 | 3.37 | 600 | 95 | 5 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V6 | 3.53 | 3.67 | 600 | 90 | 5 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V9 | 3.82 | 3.98 | 600 | 90 | 3 | 1 | -3.5 | 0 | 450 | 6.0 |
| 4V3 | 4.21 | 4.39 | 600 | 90 | 3 | 1 | -3.5 | 0 | 450 | 6.0 |
| 4V7 | 4.61 | 4.79 | 500 | 80 | 3 | 2 | -3.5 | 0.2 | 300 | 6.0 |
| 5V1 | 5.00 | 5.20 | 480 | 60 | 2 | 2 | -2.7 | 1.2 | 300 | 6.0 |
| 5V6 | 5.49 | 5.71 | 400 | 40 | 1 | 2 | -2.0 | 2.5 | 300 | 6.0 |
| 6V2 | 6.08 | 6.32 | 150 | 10 | 3 | 4 | 0.4 | 3.7 | 200 | 6.0 |
| 6V8 | 6.66 | 6.94 | 80 | 15 | 2 | 4 | 1.2 | 4.5 | 200 | 6.0 |
| 7V5 | 7.35 | 7.65 | 80 | 15 | 1 | 5 | 2.5 | 5.3 | 150 | 4.0 |
| 8V2 | 8.04 | 8.36 | 80 | 15 | 0.70 | 5 | 3.2 | 6.2 | 150 | 4.0 |
| 9V1 | 8.92 | 9.28 | 100 | 15 | 0.50 | 6 | 3.8 | 7.0 | 150 | 3.0 |
| 10 | 9.80 | 10.20 | 150 | 20 | 0.20 | 7 | 4.5 | 8.0 | 90 | 3.0 |
| 11 | 10.80 | 11.20 | 150 | 20 | 0.10 | 8 | 5.4 | 9.0 | 85 | 2.5 |
| 12 | 11.80 | 12.20 | 150 | 25 | 0.10 | 8 | 6.0 | 10.0 | 85 | 2.5 |
| 13 | 12.70 | 13.30 | 170 | 30 | 0.10 | 8 | 7.0 | 11.0 | 80 | 2.5 |
| 15 | 14.70 | 15.30 | 200 | 30 | 0.05 | 10.5 | 9.2 | 13.0 | 75 | 2.0 |
| 16 | 15.70 | 16.30 | 200 | 40 | 0.05 | 11.2 | 10.4 | 14.0 | 75 | 1.5 |
| 18 | 17.60 | 18.40 | 225 | 45 | 0.05 | 12.6 | 12.4 | 16.0 | 70 | 1.5 |
| 20 | 19.6 | 20.4 | 225 | 55 | 0.05 | 14.0 | 14.4 | 18.0 | 60 | 1.5 |
| 22 | 21.6 | 22.4 | 250 | 55 | 0.05 | 15.4 | 16.4 | 20.0 | 60 | 1.25 |
| 24 | 23.5 | 24.5 | 250 | 70 | 0.05 | 16.8 | 18.4 | 22.0 | 55 | 1.25 |

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$ [2] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ °C}$ prior to surge

Table 9. Characteristics per type; BZB84-B27 to BZB84-B75

$T_j = 25\text{ °C}$ unless otherwise specified.

| BZB84-Bxxx | Working voltage V_Z (V) | | Differential resistance r_{dif} (Ω) | | Reverse current I_R (μ A) | | Temperature coefficient S_Z (mV/K) | | Diode capacitance C_d (pF) ^[1] | Non-repetitive peak reverse current I_{ZSM} (A) ^[2] |
|------------|---------------------------|------|--|---------------------|----------------------------------|-----------|--------------------------------------|------|---|--|
| | $I_Z = 2\text{ mA}$ | | $I_Z = 0.5\text{ mA}$ | $I_Z = 2\text{ mA}$ | Max | V_R (V) | $I_Z = 2\text{ mA}$ | | | |
| | Min | Max | Max | Max | | | Min | Max | Max | Max |
| 27 | 26.5 | 27.5 | 300 | 80 | 0.05 | 18.9 | 21.4 | 25.3 | 50 | 1.00 |
| 30 | 29.4 | 30.6 | 300 | 80 | 0.05 | 21.0 | 24.4 | 29.4 | 50 | 1.00 |
| 33 | 32.3 | 33.7 | 325 | 80 | 0.05 | 23.1 | 27.4 | 33.4 | 45 | 0.90 |
| 36 | 35.3 | 36.7 | 350 | 90 | 0.05 | 25.2 | 30.4 | 37.4 | 45 | 0.80 |
| 39 | 38.2 | 39.8 | 350 | 130 | 0.05 | 27.3 | 33.4 | 41.2 | 45 | 0.70 |
| 43 | 42.1 | 43.9 | 375 | 150 | 0.05 | 30.1 | 37.6 | 46.6 | 40 | 0.60 |
| 47 | 46.1 | 47.9 | 375 | 170 | 0.05 | 32.9 | 42.0 | 51.8 | 40 | 0.50 |
| 51 | 50.0 | 52.0 | 400 | 180 | 0.05 | 35.7 | 46.6 | 57.2 | 40 | 0.40 |
| 56 | 54.9 | 57.1 | 425 | 200 | 0.05 | 39.2 | 52.2 | 63.8 | 40 | 0.30 |
| 62 | 60.8 | 63.2 | 450 | 215 | 0.05 | 43.4 | 58.8 | 71.6 | 35 | 0.30 |
| 68 | 66.6 | 69.4 | 475 | 240 | 0.05 | 47.6 | 65.6 | 79.8 | 35 | 0.25 |
| 75 | 73.5 | 76.5 | 500 | 255 | 0.05 | 52.5 | 73.4 | 88.6 | 35 | 0.20 |

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$

[2] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ °C}$ prior to surge

Table 10. Characteristics per type; BZB84-C2V4 to BZB84-C24

 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

| BZB84-Cxxx | Working voltage V_Z (V) | | Differential resistance r_{dif} (Ω) | | Reverse current I_R (μA) | | Temperature coefficient S_Z (mV/K) | | Diode capacitance C_d (pF) ^[1] | Non-repetitive peak reverse current I_{ZSM} (A) ^[2] |
|------------|------------------------------|------|--|---------------------|--|-----------|---|------|--|---|
| | $I_Z = 5\text{ mA}$ | | $I_Z = 1\text{ mA}$ | $I_Z = 5\text{ mA}$ | Max | V_R (V) | $I_Z = 5\text{ mA}$ | | | |
| | Min | Max | Max | Max | | | Min | Max | Max | Max |
| 2V4 | 2.2 | 2.6 | 600 | 100 | 50 | 1 | -3.5 | 0 | 450 | 6.0 |
| 2V7 | 2.5 | 2.9 | 600 | 100 | 20 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V0 | 2.8 | 3.2 | 600 | 95 | 10 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V3 | 3.1 | 3.5 | 600 | 95 | 5 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V6 | 3.4 | 3.8 | 600 | 90 | 5 | 1 | -3.5 | 0 | 450 | 6.0 |
| 3V9 | 3.7 | 4.1 | 600 | 90 | 3 | 1 | -3.5 | 0 | 450 | 6.0 |
| 4V3 | 4.0 | 4.6 | 600 | 90 | 3 | 1 | -3.5 | 0 | 450 | 6.0 |
| 4V7 | 4.4 | 5.0 | 500 | 80 | 3 | 2 | -3.5 | 0.2 | 300 | 6.0 |
| 5V1 | 4.8 | 5.4 | 480 | 60 | 2 | 2 | -2.7 | 1.2 | 300 | 6.0 |
| 5V6 | 5.2 | 6.0 | 400 | 40 | 1 | 2 | -2.0 | 2.5 | 300 | 6.0 |
| 6V2 | 5.8 | 6.6 | 150 | 10 | 3 | 4 | 0.4 | 3.7 | 200 | 6.0 |
| 6V8 | 6.4 | 7.2 | 80 | 15 | 2 | 4 | 1.2 | 4.5 | 200 | 6.0 |
| 7V5 | 7.0 | 7.9 | 80 | 15 | 1 | 5 | 2.5 | 5.3 | 150 | 4.0 |
| 8V2 | 7.7 | 8.7 | 80 | 15 | 0.70 | 5 | 3.2 | 6.2 | 150 | 4.0 |
| 9V1 | 8.5 | 9.6 | 100 | 15 | 0.50 | 6 | 3.8 | 7.0 | 150 | 3.0 |
| 10 | 9.4 | 10.6 | 150 | 20 | 0.20 | 7 | 4.5 | 8.0 | 90 | 3.0 |
| 11 | 10.4 | 11.6 | 150 | 20 | 0.10 | 8 | 5.4 | 9.0 | 85 | 2.5 |
| 12 | 11.4 | 12.7 | 150 | 25 | 0.10 | 8 | 6.0 | 10.0 | 85 | 2.5 |
| 13 | 12.4 | 14.1 | 170 | 30 | 0.10 | 8 | 7.0 | 11.0 | 80 | 2.5 |
| 15 | 13.8 | 15.6 | 200 | 30 | 0.05 | 10.5 | 9.2 | 13.0 | 75 | 2.0 |
| 16 | 15.3 | 17.1 | 200 | 40 | 0.05 | 11.2 | 10.4 | 14.0 | 75 | 1.5 |
| 18 | 16.8 | 19.1 | 225 | 45 | 0.05 | 12.6 | 12.4 | 16.0 | 70 | 1.5 |
| 20 | 18.8 | 21.2 | 225 | 55 | 0.05 | 14.0 | 14.4 | 18.0 | 60 | 1.5 |
| 22 | 20.8 | 23.3 | 250 | 55 | 0.05 | 15.4 | 16.4 | 20.0 | 60 | 1.25 |
| 24 | 22.8 | 25.6 | 250 | 70 | 0.05 | 16.8 | 18.4 | 22.0 | 55 | 1.25 |

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$ [2] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge

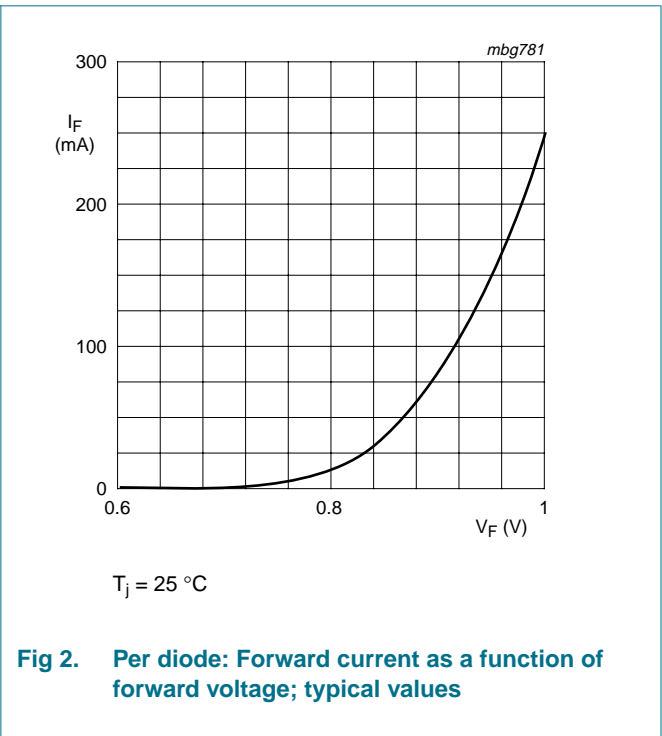
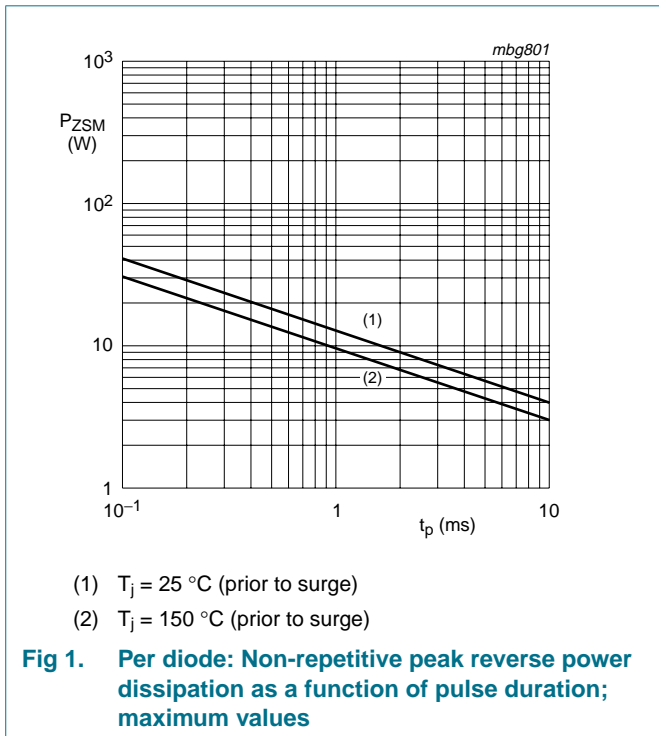
Table 11. Characteristics per type; BZB84-C27 to BZB84-C75

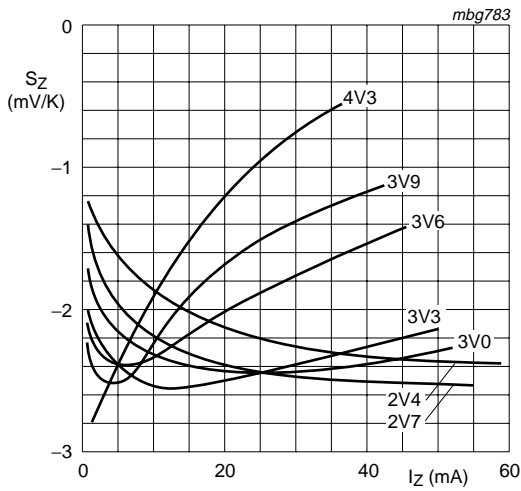
$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

| BZB84-Cxxx | Working voltage V_Z (V) | | Differential resistance r_{dif} (Ω) | | Reverse current I_R (μA) | | Temperature coefficient S_Z (mV/K) | | Diode capacitance C_d (pF) ^[1] | Non-repetitive peak reverse current I_{ZSM} (A) ^[2] |
|------------|---------------------------|------|--|---------------------|---|---------------------|--------------------------------------|------|---|--|
| | $I_Z = 2\text{ mA}$ | | $I_Z = 0.5\text{ mA}$ | $I_Z = 2\text{ mA}$ | V_R (V) | $I_Z = 2\text{ mA}$ | | | | |
| | Min | Max | Max | Max | | Max | Min | Max | Max | Max |
| 27 | 25.1 | 28.9 | 300 | 80 | 0.05 | 18.9 | 21.4 | 25.3 | 50 | 1.00 |
| 30 | 28.0 | 32.0 | 300 | 80 | 0.05 | 21.0 | 24.4 | 29.4 | 50 | 1.00 |
| 33 | 31.0 | 35.0 | 325 | 80 | 0.05 | 23.1 | 27.4 | 33.4 | 45 | 0.90 |
| 36 | 34.0 | 38.0 | 350 | 90 | 0.05 | 25.2 | 30.4 | 37.4 | 45 | 0.80 |
| 39 | 37.0 | 41.0 | 350 | 130 | 0.05 | 27.3 | 33.4 | 41.2 | 45 | 0.70 |
| 43 | 40.0 | 46.0 | 375 | 150 | 0.05 | 30.1 | 37.6 | 46.6 | 40 | 0.60 |
| 47 | 44.0 | 50.0 | 375 | 170 | 0.05 | 32.9 | 42.0 | 51.8 | 40 | 0.50 |
| 51 | 48.0 | 54.0 | 400 | 180 | 0.05 | 35.7 | 46.6 | 57.2 | 40 | 0.40 |
| 56 | 52.0 | 60.0 | 425 | 200 | 0.05 | 39.2 | 52.2 | 63.8 | 40 | 0.30 |
| 62 | 58.0 | 66.0 | 450 | 215 | 0.05 | 43.4 | 58.8 | 71.6 | 35 | 0.30 |
| 68 | 64.0 | 72.0 | 475 | 240 | 0.05 | 47.6 | 65.6 | 79.8 | 35 | 0.25 |
| 75 | 70.0 | 79.0 | 500 | 255 | 0.05 | 52.5 | 73.4 | 88.6 | 35 | 0.20 |

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$

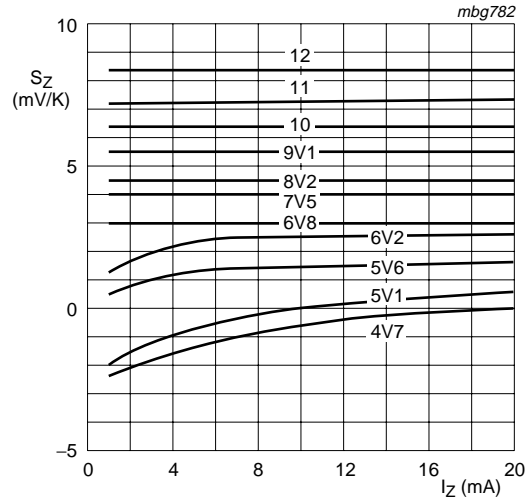
[2] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge





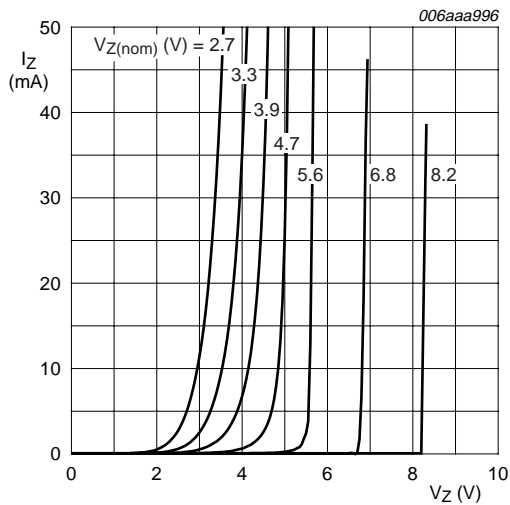
$T_j = 25\text{ }^\circ\text{C to }150\text{ }^\circ\text{C}$
BZB84-B/C2V4 to BZB84-B/C4V3

Fig 3. Per diode: Temperature coefficient as a function of working current; typical values



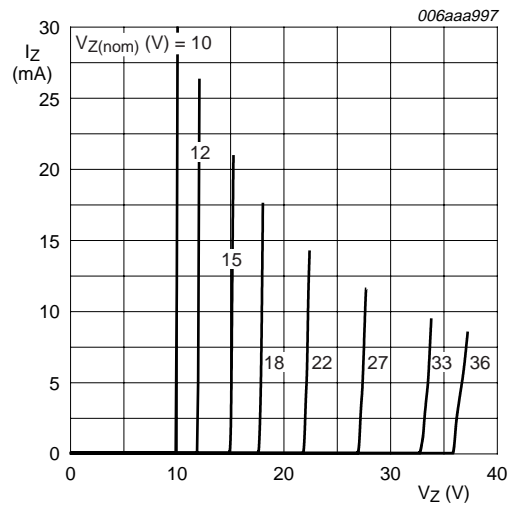
$T_j = 25\text{ }^\circ\text{C to }150\text{ }^\circ\text{C}$
BZB84-B/C4V7 to BZB84-B/C12

Fig 4. Per diode: Temperature coefficient as a function of working current; typical values



$T_j = 25\text{ }^\circ\text{C}$
BZB84-B/C2V7 to BZB84-B/C8V2

Fig 5. Per diode: Working current as a function of working voltage; typical values



$T_j = 25\text{ }^\circ\text{C}$
BZB84-B/C10 to BZB84-B/C36

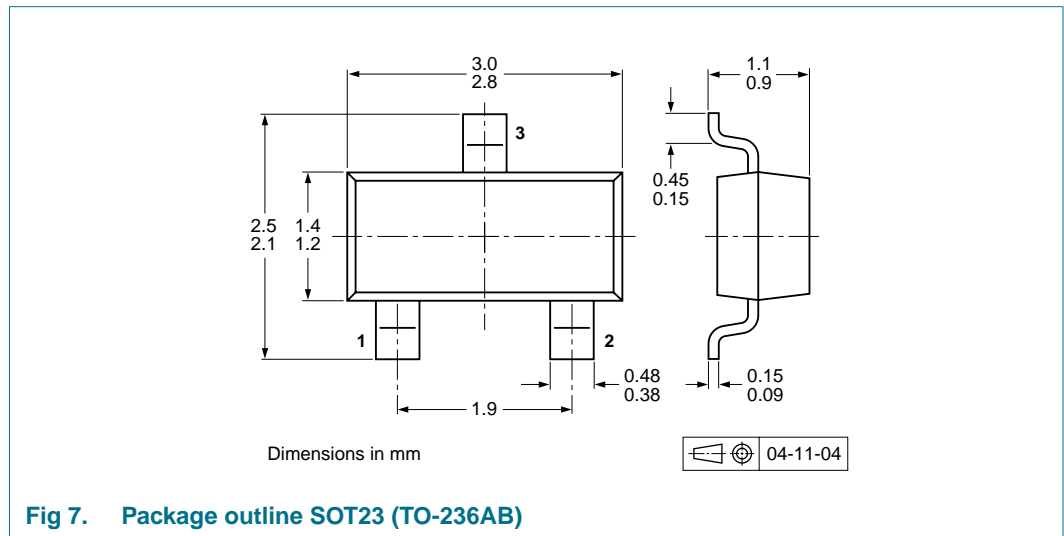
Fig 6. Per diode: Working current as a function of working voltage; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 12. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

| Type number | Package | Description | Packing quantity | |
|--|---------|--------------------------------|------------------|-------|
| | | | 3000 | 10000 |
| BZB84-B2V4 to BZB84-C75 ^[2] | SOT23 | 4 mm pitch, 8 mm tape and reel | -215 | -235 |

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

11. Soldering

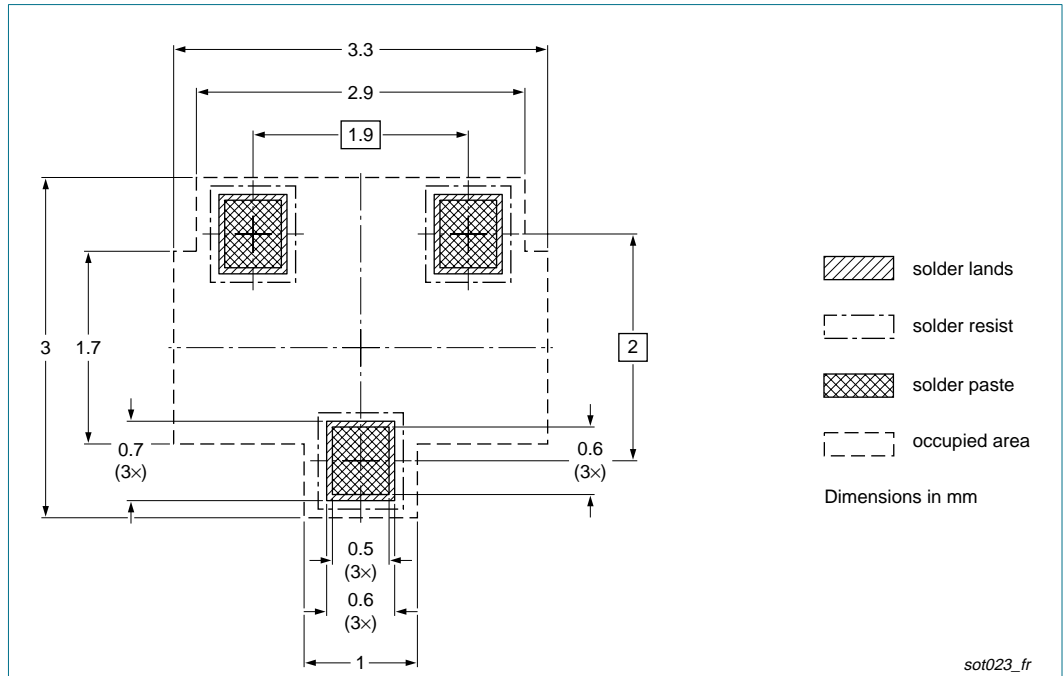


Fig 8. Reflow soldering footprint SOT23 (TO-236AB)

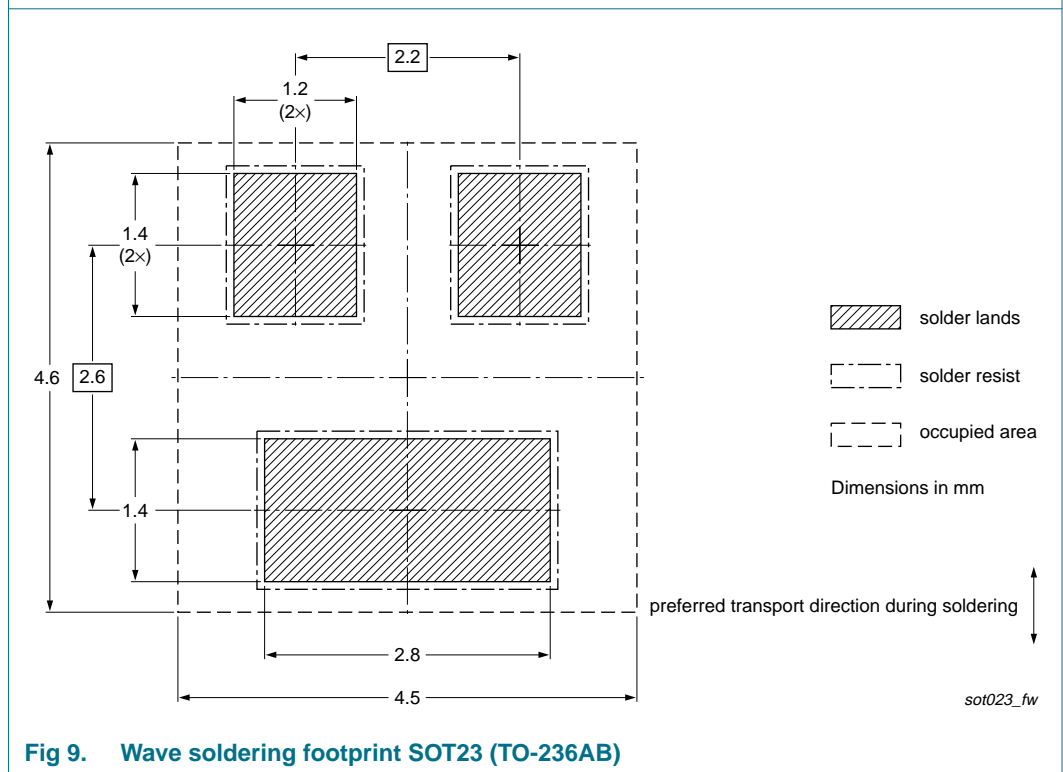


Fig 9. Wave soldering footprint SOT23 (TO-236AB)

12. Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|---|---------------|-------------|
| BZB84_SER_3 | 20090609 | Product data sheet | - | BZB84_SER_2 |
| Modifications: | | <ul style="list-style-type: none">• Table 5 “Limiting values”: P_{tot} maximum value amended• Table 6: R_{th} maximum values amended• Section 13 “Legal information”: updated | | |
| BZB84_SER_2 | 20090223 | Product data sheet | - | BZB84_SER_1 |
| BZB84_SER_1 | 20080514 | Product data sheet | - | - |

13. Legal information

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| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
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[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 9 June 2009

Document identifier: BZB84_SER_3

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